

SOD-323 Plastic-Encapsulate Diode
PRODUCT SUMMARY

RB551V-30 Schottky Diodes

FEATURES

 High current rectifier Schottky diode
 Low voltage, low inductance
 For power supply

MARKING: D
SOD-323


Pb-free; RoHS-compliant
MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

 Single Diode @ $T_A = 25^\circ\text{C}$

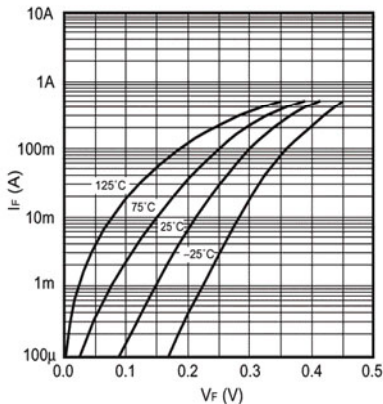
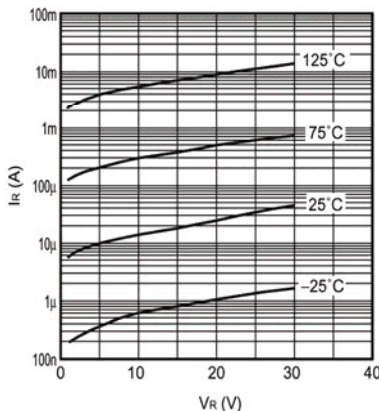
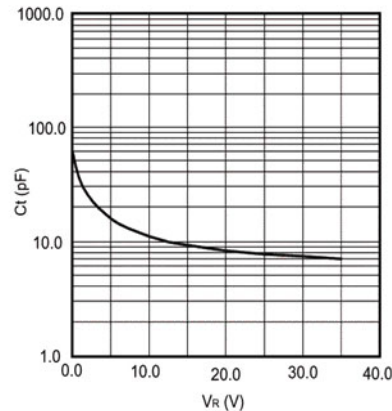
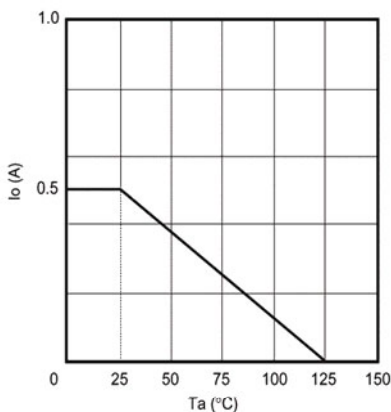
Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	30	V
DC reverse voltage	V_R	20	V
Mean rectifying current	I_O	0.5	A
Peak forward surge current	I_{FSM}	2	A
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-40~+125	$^\circ\text{C}$

ELECTRICAL RATINGS

 @ $T_A = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F			0.36 0.47	V	$I_F=100\text{mA}$ $I_F=500\text{mA}$
Reverse current	I_R			100	μA	$V_R=20\text{V}$

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TYPICAL CHARACTERISTICS

 Electrical Characteristic curves ($T_a = 25^\circ\text{C}$)

Fig.1 Forward characteristics

Fig.2 Reverse characteristics

Fig.3 Capacitance between terminals characteristics

Fig.4 Derating curve

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